

Notice of References Cited

 Application/Control No.
 09/536,087

 Applicant(s)/Patent Under
 Reexamination
 Li et al.

 Examiner
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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification	
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*	B	US-4,863,755-B1	09-1989	Hess et al.	427	574
*	C	US-5,234,869-B1	08-1993	Mikata et al.	438	793
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	N	EP-0464515-	01-1992	EP	Mikata et al.	H01L 21/318
	O	EP-0771886-	05-1997	EP	Loboda	C23C 16/36
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages
	U	Loboda et al., "Using Trimethylsilane to Improve Safety, Throughput and Versatility in PECVD Processes", Electrochemical Proceedings, vol. 97-10, pages 443-453. <i>Cited in Paper # 13</i>
	V	Laxman et al., "Synthesizing Low k CVD materials for Fab Use", Semiconductor International (Nov 2000), pages 95-102. <i>Cited in Paper # 13</i>
	W	Anonymous, "New Gas Helps Make Faster ICs", Machine Design, (Nov 4, 1999), page 118. <i>Cited in Paper # 13</i>
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.